Electronic Supplementary Material (ESI) for Nanoscale.

Supplementary Information

Low-Temperature-Annealed and UV-Ozone-Enhanced Combustion Derived Nickel Oxide Hole Injection Layer for Flexible Quantum Dot Light-Emitting Diodes

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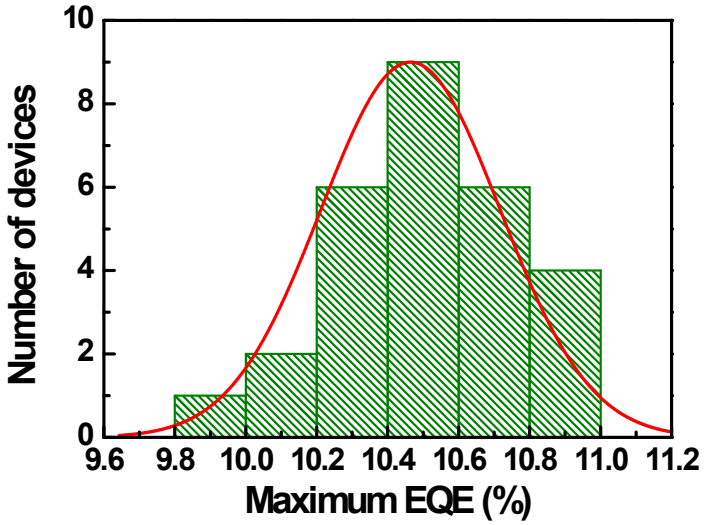

Figure S1. Histogram of maximum EQE of 28 QLEDs based on 20 min UVO treatment from different batches.

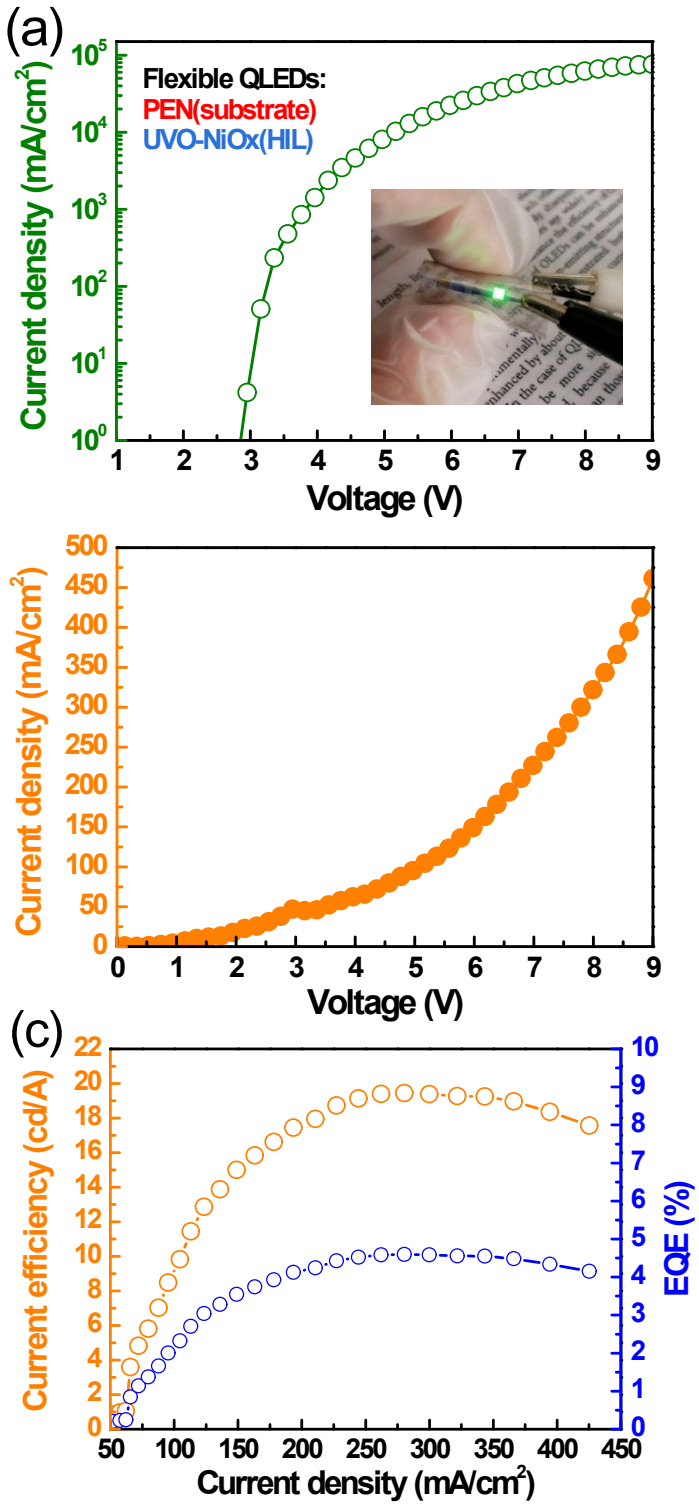

Figure S2. (a) L-V characteristics of the flexible QLEDs based on combustion derived NiOx HILs. The inset shows the photograph of the device working at a highly bent state with uniform emission. (b) J-V and (c) CE-J-EQE characteristics of the flexible QLEDs based on UVO-NiO_x HILs.

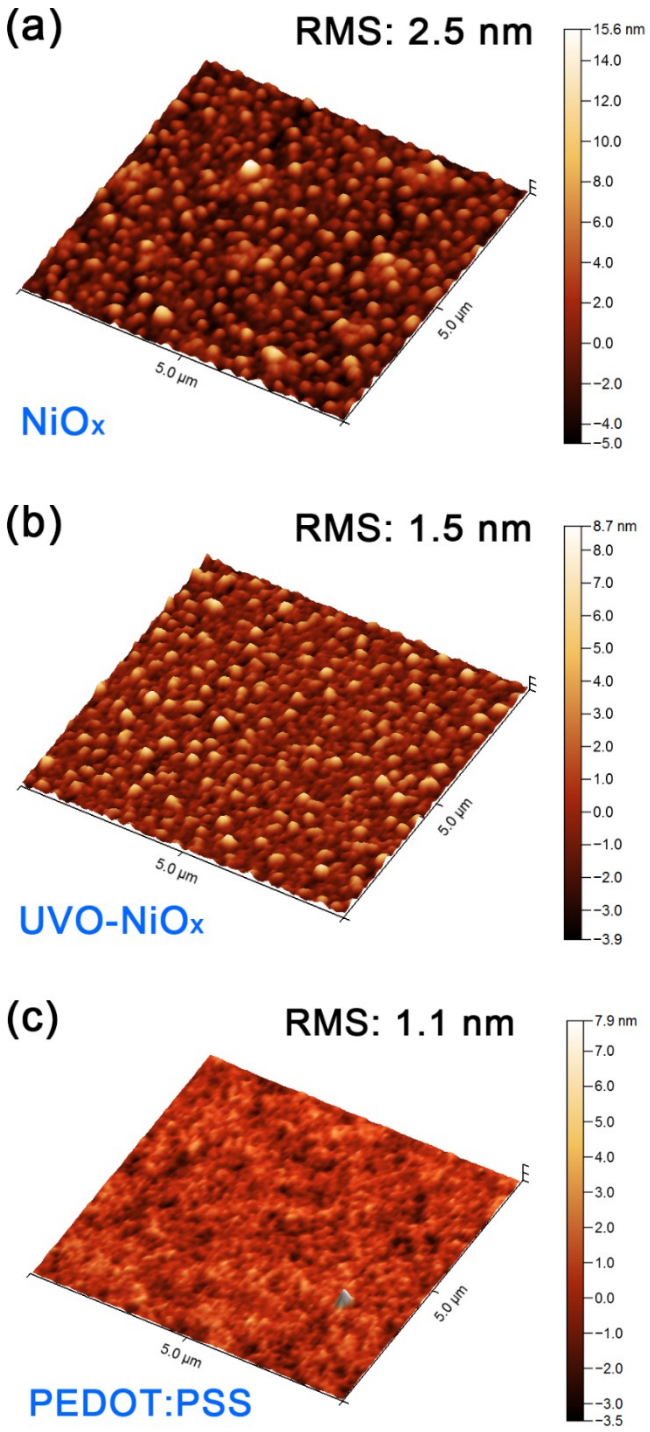

Figure S3. 3D AFM topography comparison of the (a) pristine NiO_x, (b) UVO-NiO_x, and (c) PEDOT:PSS films.